

Inventor: Eugene P. Marsh
Title: Platinum-containing Integrated Circuits and Capacitor Constructions
Assignee: Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT

PURSUANT TO 37 C.F.R. §§1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449.

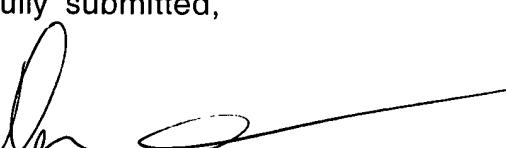
The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation of co-pending application Serial No. 09/421,625 filed October 19, 1999. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. §1.98(d) and MPEP §609(2). No admission is made regarding whether all the submitted references are prior art.

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: 8/13/03

Attorney:


David G. Latwesen, Ph.D.
Reg. #38,533
WELLS ST. JOHN P.S.

LIST OF ART CITED BY APPLICANT

(Use several sheets if necessary)

APPLICANT
Micron Technology, Inc.PRIORITY FILING DATE
10/19/99PRIORITY GROUP
Unknown

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	4,341,662	7/82	Pfefferle			
	AB	4,431,750	2/84	McGinnis et al.			
	AC	4,714,693	12/87	Targos			
	AD	3,975,304	8/76	della Porta et al.			
	AE	3,856,709	12/74	Porta et al.			
	AF	5,525,570	6/96	Chakraborty et al.			
	AG	5,330,700	7/94	Soukup et al.			
	AH	4,719,442	1/88	Bohara et al.			

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AI	9-082666		Japan				
	AJ	0 415 751 A1		EPO				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AK		Ju-Hong Kwan et al.; "Characterization of Pt Thin Films Deposited by Metallorganic Chemical Vapor Deposition for Ferroelectric Bottom Electrodes"; J. Electrochem. Soc., Vol. 144, No. 8, August 1997; pp. 2848-2854					
	AL		M. Ino et al.; "Rugged surface polycrystalline silicon film deposition and its application in a stacked dynamic random access memory capacitor electrode"; J. Vac. Sci. Technol. B 14(2), March/April 1996; pp. 751-756					
	AM							
	AN							
	AO							

EXAMINER	DATE CONSIDERED
----------	-----------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

EV318283583

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-2382		PRIORITY SERIAL NO. Filed Herewith		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Micron Technology, Inc.				
					PRIORITY FILING DATE 10/19/99		PRIORITY GROUP Unknown		
		U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate	
	AA	5,639,685	6/97	Zahurak et al.					
	AB	5,917,213	6/99	Iyer et al.					
	AC	5,874,364	2/99	Nakabayashi et al.					
	AD	5,053,917	10/91	Miyasaka et al.					
	AE	5,208,479	5/93	Mathews et al.					
	AF	5,783,716	7/98	Baum et al.					
	AG	5,796,648	8/98	Kawakubo et al.					
	AH	5,763,286	6/98	Figura et al.					
FOREIGN PATENT DOCUMENTS									
		Document Number	Date	Country		Class	Subclass	Translation	
	AI	5-67730		Japan				Yes	No
	AJ	0 855 738 A2		EPO					
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)									
	AK								
	AL								
	AM								
	AN								
EXAMINER				DATE CONSIDERED					
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>									

LIST OF ART CITED BY APPLICANT

(Use several sheets if necessary)

APPLICANT
Micron Technology, Inc.PRIORITY FILING DATE
10/19/99PRIORITY GROUP
Unknown

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,320,978	6/94	Hsu			
	AB	6,033,953	3/00	Aoki et al.			
	AC	5,990,559	11/99	Marsh			
	AD	4,425,261	1/84	Stenius et al.			
	AE	6,175,129	1/01	Liu et al.			
	AF	6,010,744	1/00	Buskirk et al.			
	AG	5,555,486	9/96	Kingon et al.			
	AH	6,232,629	5/01	Nakamura			
	AI	5,635,420	6/97	Nishioka			
	AJ						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AK	JP 9051079	2/18/97	Japan				
	AL	JP 8017939	6/3/03	Japan				
	AM	JP 10173149	6/26/98	Japan				
	AN	JP 10180098	7/7/98	Japan				
	AO							
	AP							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AQ		
	AR		
	AS		

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.